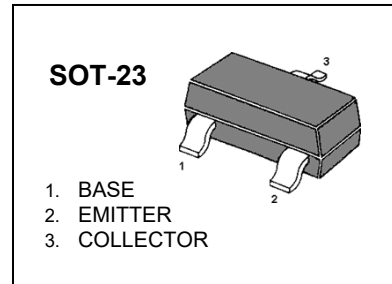


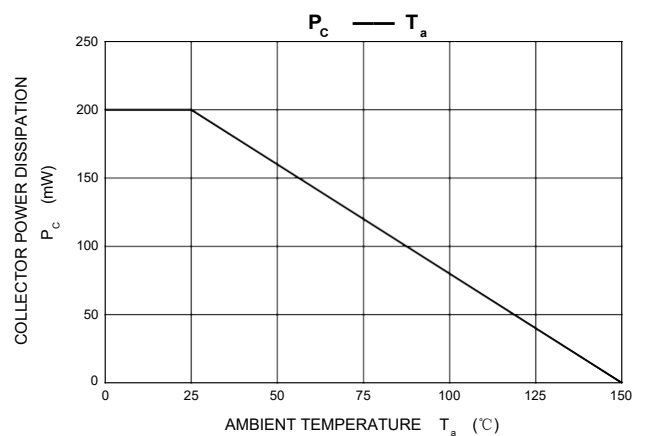
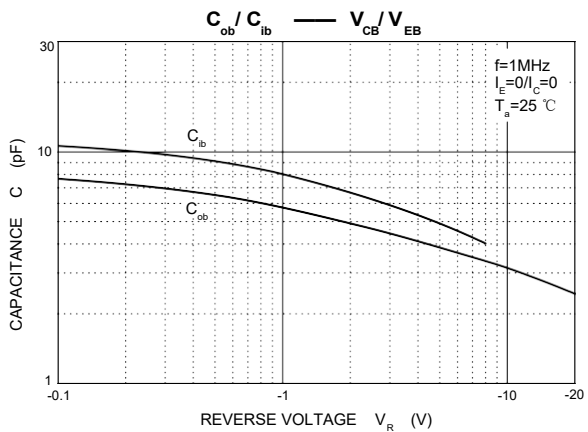
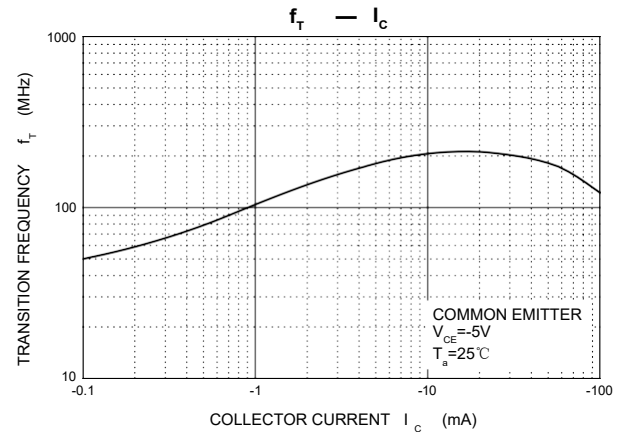
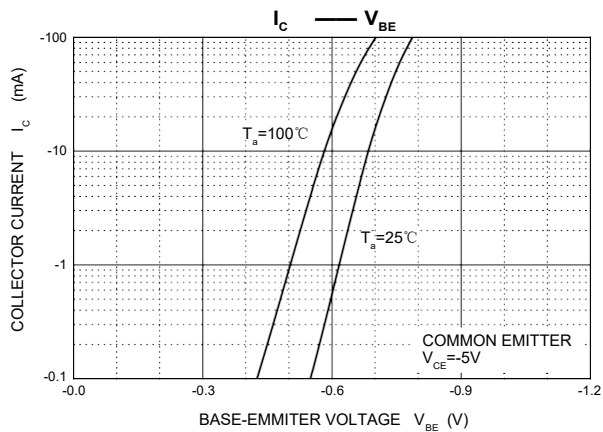
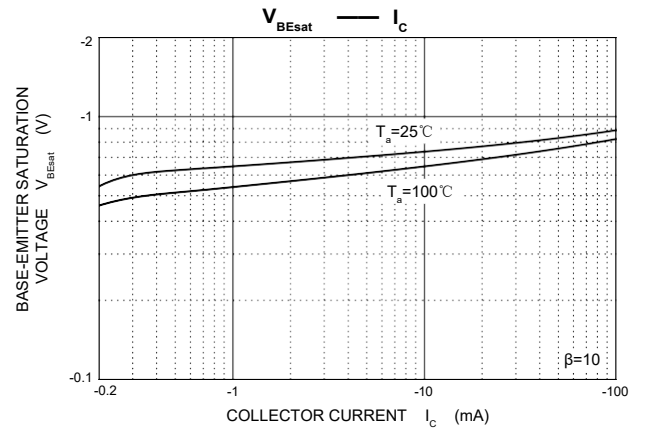
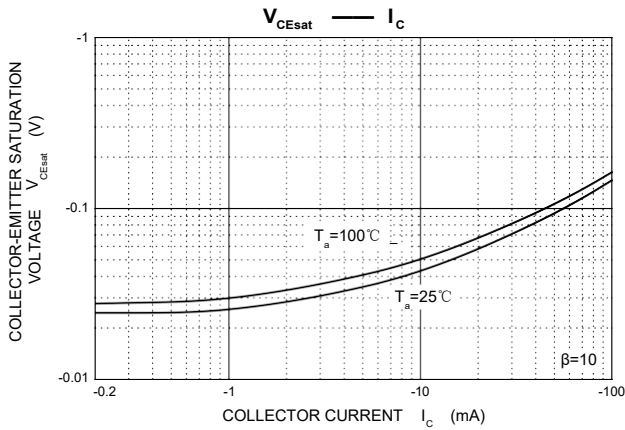
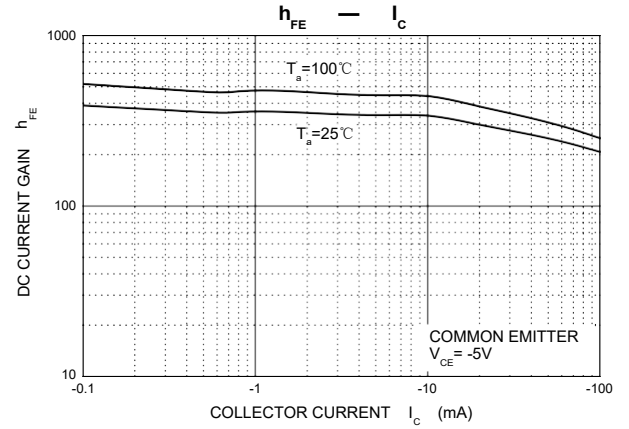
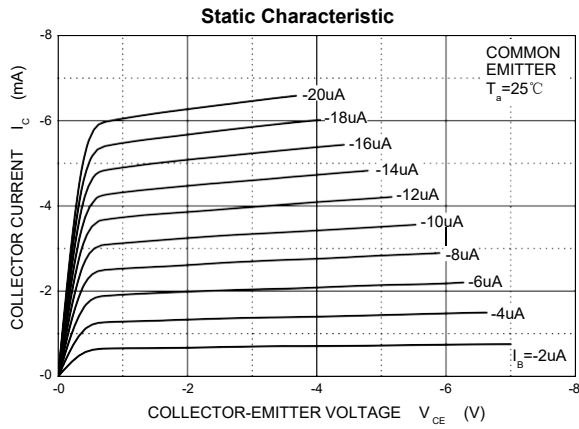
**S9015 TRANSISTOR(PNP)****FEATURES****Complementary to S9014****MARKING: M6****MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	-50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-45	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-0.1	A
P <sub>C</sub>	Collector Power Dissipation	0.2	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -100μA, I <sub>E</sub> = 0	-50			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -0.1mA, I <sub>B</sub> = 0	-45			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -100μA, I <sub>C</sub> = 0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -50V, I <sub>E</sub> = 0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0			-0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -1mA	200		450	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA			-0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA f = 30MHz	150			MHz

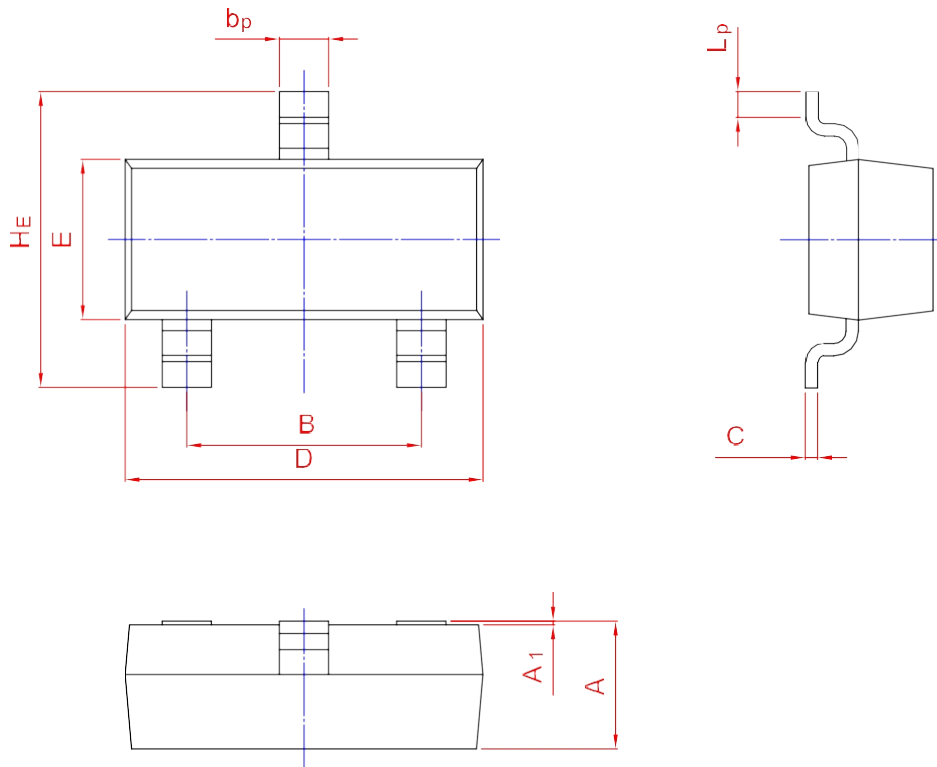
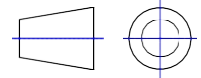
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b <sub>p</sub>	C	D	E	H <sub>E</sub>	A <sub>1</sub>	L <sub>p</sub>
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20